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Inclosure Material:

Metal

Overall Length:

0.520 inches

Overall Diameter:

1.250 inches

Mounting Facility Quantity:

1

Internal Configuration:

Junction contact

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Threaded stud

Features Provided:

Hermetically sealed case

Thread Size:

0.190 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

100.0 breakdown voltage, collector-to-base, emitter open and 55.0 breakdown voltage, collector-to-emitter, base open and 10.0

breakdown voltage, emitter-to-base, collector open

Current Rating Per Characteristic:

Between 3.00 amperes source cutoff current and 6.00 amperes source cutoff current

Power Rating Per Characteristic:

75.0 watts small-signal input power, common-collector

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Special Features:

Junction pattern arrangement: npn

Thread Series Designator:

Unf

Terminal Type And Quantity:

3 tab, solder lug

Specification Data:

80131-release3099 professional/industrial association specification

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

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Fiig: A110a0

